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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/790,816	03/03/2004	Terry L. Gilton	M4065.0607/P607-A	1483	
24998	7590 10/31/2005		EXAM	INER	
DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2101 L Street, NW Washington, DC 20037			DOTY, HEAT	DOTY, HEATHER ANNE	
			ART UNIT	PAPER NUMBER	
w asimigron,	DC 20037		2813	-	
			DATE MAILED: 10/31/200	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

		AV.			
	Application No.	Applicant(s)			
	10/790,816	GILTON, TERRY L.			
Office Action Summary	Examiner	Art Unit			
	Heather A. Doty	2813			
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPL' WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.11 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period v  - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).			
Status					
1)⊠ Responsive to communication(s) filed on <u>03 M</u>	arch 2004.				
<u></u>	action is non-final.				
Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims					
4) ☐ Claim(s) 27-32 is/are pending in the application 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 27-32 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	wn from consideration.				
Application Papers					
9)☐ The specification is objected to by the Examiner.					
10)⊠ The drawing(s) filed on <u>03 March 2004</u> is/are: a)⊠ accepted or b)⊡ objected to by the Examiner.					
Applicant may not request that any objection to the	* ' '	· ·			
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.					
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Application of the contraction of the contr	on No ed in this National Stage			
Attachment(s)					
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 3/03/04, 8/02/04.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:				

#### **DETAILED ACTION**

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless – (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 27-30 are rejected under 35 U.S.C. 102(b) as being anticipated by Wolstenholme et al. (U.S. 5,751,012).

Regarding claim 27, Wolstenholme et al. teaches an array of programmable conductor memories in an integrated circuit comprising pillars of stacked materials on a semiconductor substrate (Fig. 3; columns 3-6).

Regarding claim 28-30, Wolstenholme et al. teaches the array of claim 27, wherein the regions between the pillars comprise insulating material, further limited by claim 28, which comprises silicon oxide, further limited by claim 29, which comprises TEOS, further limited by claim 30 (34 in Fig. 3; column 6, lines 10-12).

### Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 31 and 32 are rejected under 35 U.S.C. 103(a) as being unpatentable over Wolstenholme et al. (U.S. 5,751,012) in view of Shroff et al. (U.S.6,515,343).

Regarding claims 31 and 32, Wolstenholme et al. teaches the array of claim 29 (note 35 U.S.C. 102(b) rejection above), and further teaches that a silicon nitride layer with a thickness of 50 nm (500 Å—column 6, lines 35-37) that comforms to the top of the pillars (33 in Fig. 3), but does not teach that the silicon nitride layer conforms to the substrate below the silicon oxide.

Shroff et al. teaches an array of antifuse pillars (101, 104, and 106 in Fig. 3), wherein the regions between the pillars comprise insulating material (110 in Fig. 3), and a silicon nitride layer that comforms to the pillars and to the region beneath the insulating material (120 in Fig 3). The silicon nitride layer protects the impurities from diffusing into the programmable layers (column 4, lines 35-56).

Therefore, at the time of the invention, it would have been obvious to one of ordinary skill in the art to form the layer of silicon nitride taught by Wolstenholme et al. so that it conforms to the pillars and the substrate beneath the insulating material, as taught by Shroff et al. The motivation for doing so at the time of the invention would have been to get better sidewall coverage for the pillars, and better protect them from impurities, as taught by Shroff et al.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Heather A. Doty, whose telephone number is 571-272-8429. The examiner can normally be reached on M-F, 8:30 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr., can be reached at 571-272-1702. The fax phone

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Art Unit: 2813

number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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